

DESCRIPTION

The DRS1AF~DRS1MF are available in SMAF package

ORDERING INFORMATION

Package Type	Part Number				
	DRS1AF				
	DRS1BF				
SMAF	DRS1DF				
	DRS1GF DRS1JF				
					DRS1KF
		DRS1MF			
Note	SPQ: 3,000pcs/Reel				
AiT provides all RoHS Compliant Products					

PIN DESCRIPTION



FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- Fast reverse recovery time
- Available in SMAF package

MECHANICAL DATA

Case: SMAF

Terminals: Solderable per MIL-STD-750,

Method 2026

Approx. Weight: 27mg 0.00086oz

DRS1AF~DRS1MF

FAST RECOVERY RECTIFIER DIODE REVERSE VOLTAGE 50V TO 1000V FORWARD CURRENT 1A

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter		Symbol	DRS1AF	DRS1BF	DRS1DF	DRS1GF	DRS1JF	DRS1KF	DRS1MF	Unit
Maximum Repetitive Peak Reverse Voltage		V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Volta	ge	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blockir	ng Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T _A =65°C		I _{F(AV)}		1.0						Α
Peak Forward Surge 8.3ms Single Half Sir Superimposed on Ra (JEDEC Method)	ne Wave	I _{FSM}	25					Α		
Maximum Instantaneous Forward Voltage at 1A		V _F		1.3						\
Maximum DC Reverse Current at Rated DC Blocking Voltage	T _A =25°C T _A =125°C	I _R		5.0 100				μΑ		
Maximum Reverse Recovery TimeNOTE1		t _{rr}	150 250 500					00	ns	
Typical Junction Capacitance ^{NOTE2}		Сл	15						pF	
Operating and Storage Temperature Range		TJ, TSTG	-55 ~150						°C	

NOTE1: Measured with I_F=0.5A, I_R=1A, I_{rr}=0.25A

NOTE2: Measured at 1MHz and applied reverse voltage of 4V D.C

TYPICAL CHARACTERISTICS

Figure. 1 Forward Current Derating Curve

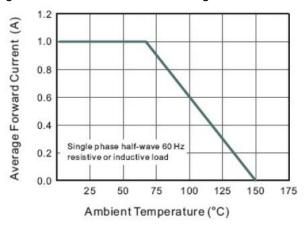


Figure. 3 Typical Instantaneous Forward

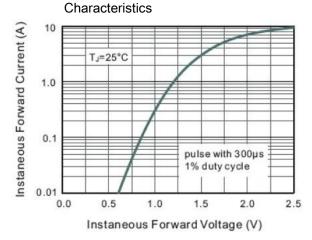


Figure. 5 Maximum Non-Repetitive Peak Forward

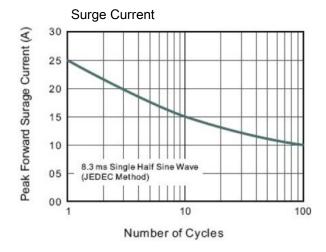


Figure. 2 Typical Reverse Characteristics

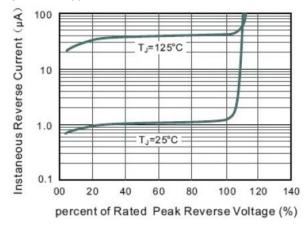
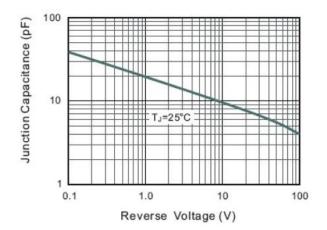


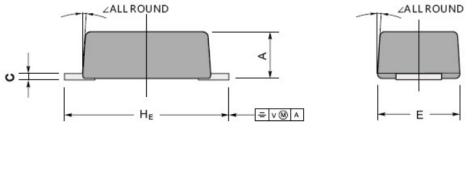
Figure. 4 Typical Junction Capacitance

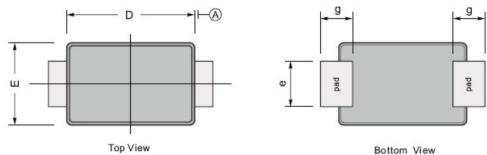


PACKAGE INFORMATION

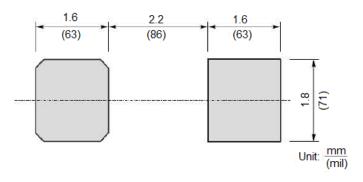
Dimension in SMAF (Unit: mm)

Plastic surface mounted package; 2 leads





The recommended mounting pad size



UN	NIT	Α	С	D	Е	е	g	HE		
mm	Max	1.1	0.20	3.7	2.7	1.6	1.2	4.9		
	Min	0.9	0.12	3.3	2.4	1.3	0.8	4.4	7 °	
mil	Max	43	7.9	146	106	63	47	193	/	
	Min	35	4.7	130	94	51	31	173		

DRS1AF~DRS1MF

FAST RECOVERY RECTIFIER DIODE

REVERSE VOLTAGE 50V TO 1000V FORWARD CURRENT 1A

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